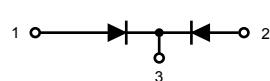




Schottky Barrier Diode Lead free product

RB715FG



FEATURES

- Extra small power mold type.
- Low V_F .
- High reliability.

APPLICATIONS

- General purpose application.

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
Diode reverse voltage	V_R	40	V
Average forward current	I_F	30	mA
Forward Surge Current $t=1\mu\text{s}$	I_{FS}	200	mA
Power Dissipation	P_d	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-40+125	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu\text{A}$	40		V
Reverse voltage leakage current	I_R	$V_R=10\text{V}$		1	μA
Forward voltage	V_F	$I_F=1\text{mA}$		370	mV
Diode capacitance	C_D	$V_R=1\text{V} f=1\text{MHz}$		2.0	pF



RB715FG

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

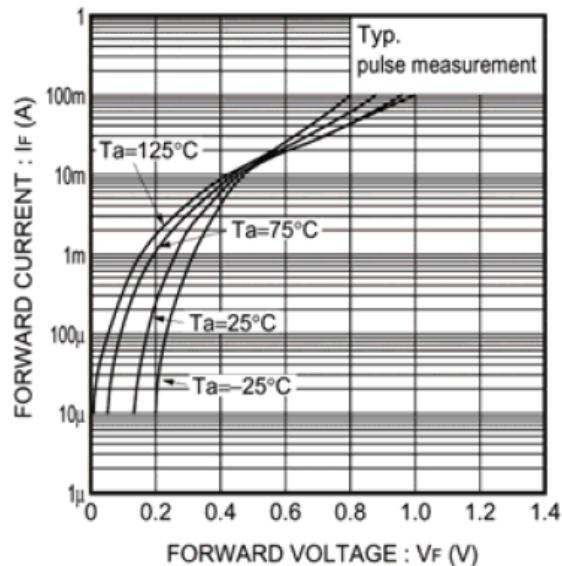


Fig. 1 Forward characteristics

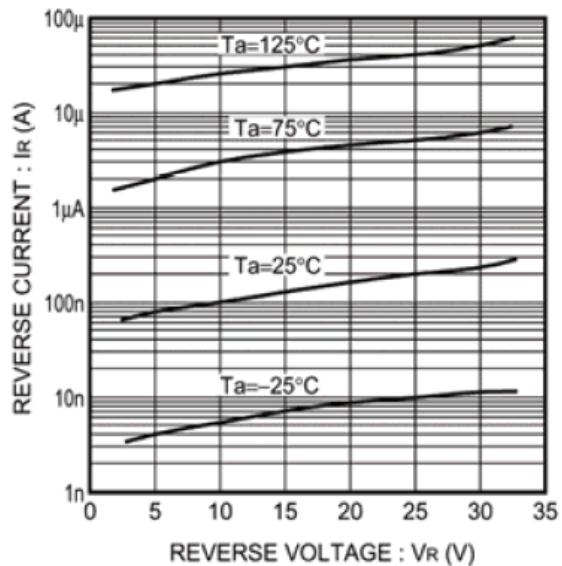


Fig. 2 Reverse characteristics

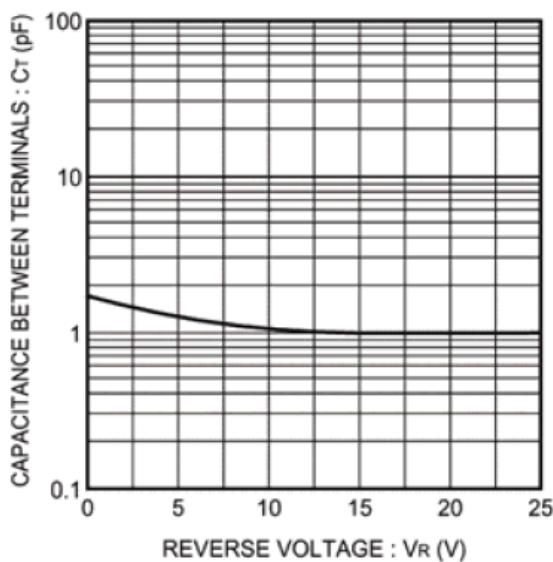


Fig. 3 Capacitance between terminals characteristics

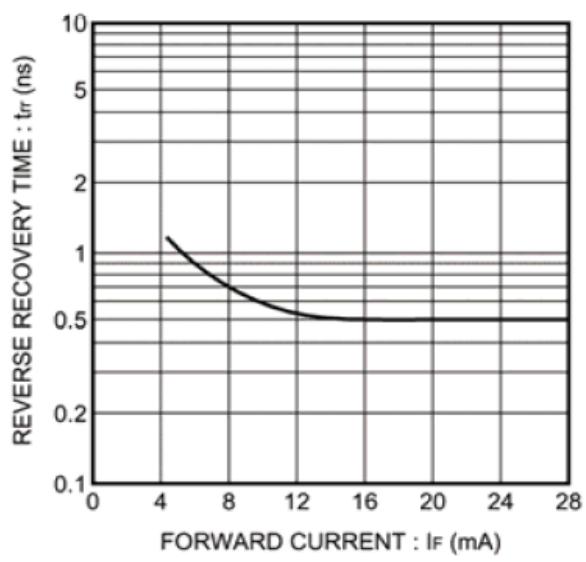


Fig. 4 Reverse recovery time characteristics